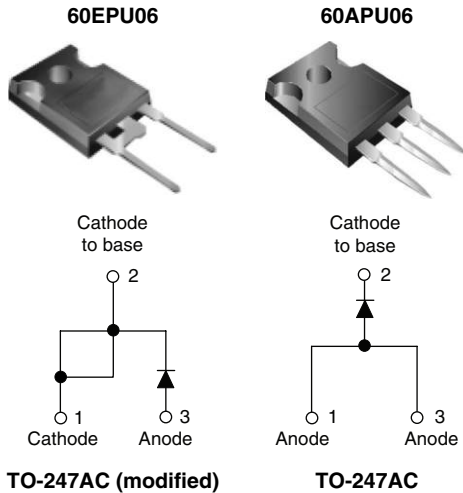


## Ultrafast Soft Recovery Diode, 60 A FRED Pt™



### FEATURES

- Ultrafast recovery
- 175 °C operating junction temperature
- Designed and qualified for industrial level

### BENEFITS

- Reduced RFI and EMI
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

### DESCRIPTION/APPLICATIONS

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems.

The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for HF welding, power converters and other applications where switching losses are not significant portion of the total losses.

### PRODUCT SUMMARY

$t_{rr}$ (typical)	34 ns
$I_{F(AV)}$	60 A
$V_R$	600 V

### ABSOLUTE MAXIMUM RATINGS

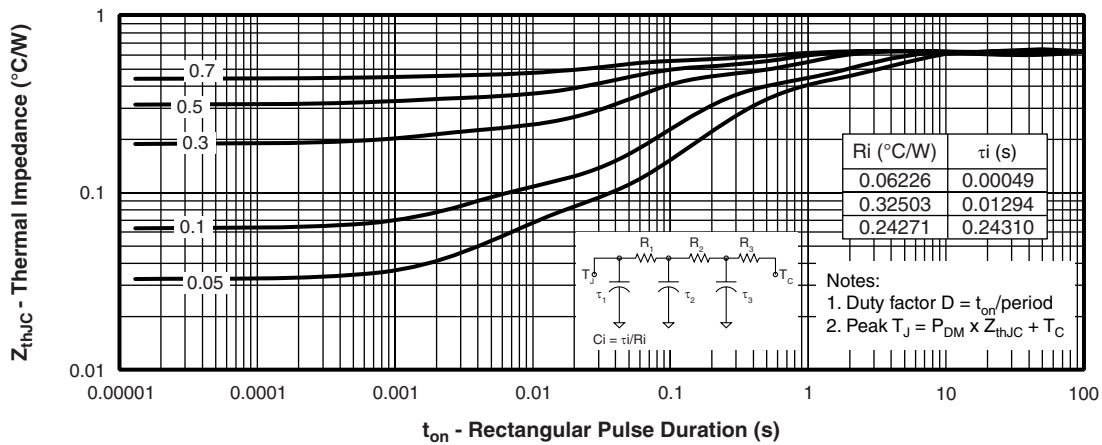
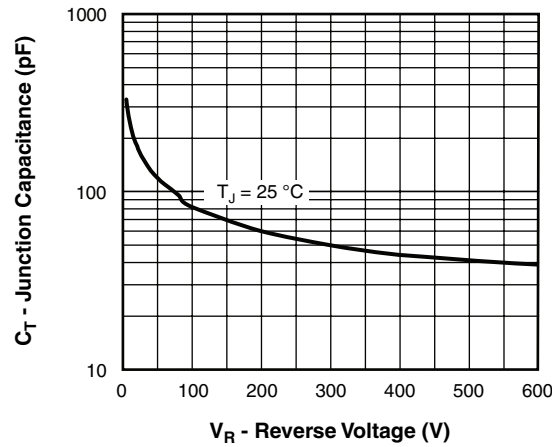
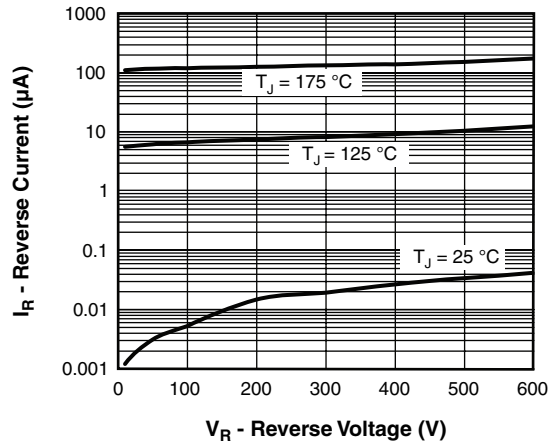
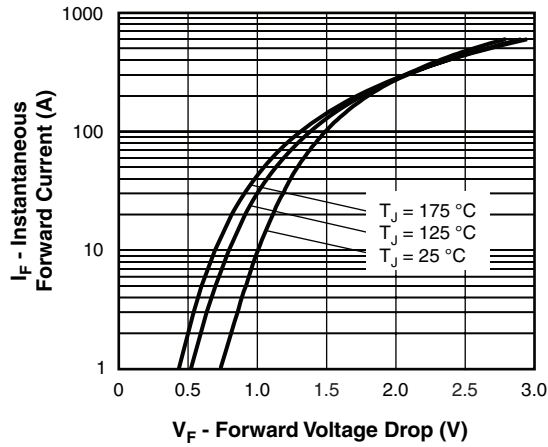
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Cathode to anode voltage	$V_R$		600	V
Continuous forward current	$I_{F(AV)}$	$T_C = 116\text{ °C}$	60	A
Single pulse forward current	$I_{FSM}$	$T_C = 25\text{ °C}$	600	
Maximum repetitive forward current	$I_{FRM}$	Square wave, 20 kHz	120	
Operating junction and storage temperatures	$T_J, T_{Stg}$		- 55 to 175	°C

### ELECTRICAL SPECIFICATIONS ( $T_J = 25\text{ °C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	$V_{BR}, V_r$	$I_R = 100\ \mu\text{A}$	600	-	-	V
Forward voltage	$V_F$	$I_F = 60\text{ A}$	-	1.35	1.68	
		$I_F = 60\text{ A}, T_J = 125\text{ °C}$	-	1.20	1.42	
		$I_F = 60\text{ A}, T_J = 175\text{ °C}$	-	1.11	1.30	
Reverse leakage current	$I_R$	$V_R = V_R\text{ rated}$	-	-	50	$\mu\text{A}$
		$T_J = 150\text{ °C}, V_R = V_R\text{ rated}$	-	-	500	
Junction capacitance	$C_T$	$V_R = 600\text{ V}$	-	39	-	pF

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Reverse recovery time	$t_{rr}$	$I_F = 1\text{ A}$ , $dI_F/dt = 200\text{ A}/\mu\text{s}$ , $V_R = 30\text{ V}$	-	34	45	ns	
		$T_J = 25\text{ }^\circ\text{C}$	-	81	-		
		$T_J = 125\text{ }^\circ\text{C}$	-	164	-		
Peak recovery current	$I_{RRM}$	$I_F = 60\text{ A}$ $dI_F/dt = 200\text{ A}/\mu\text{s}$ $V_R = 200\text{ V}$	$T_J = 25\text{ }^\circ\text{C}$	-	7.4	-	A
			$T_J = 125\text{ }^\circ\text{C}$	-	17.0	-	
Reverse recovery charge	$Q_{rr}$	$I_F = 60\text{ A}$ $dI_F/dt = 200\text{ A}/\mu\text{s}$ $V_R = 200\text{ V}$	$T_J = 25\text{ }^\circ\text{C}$	-	300	-	nC
			$T_J = 125\text{ }^\circ\text{C}$	-	1394	-	

<b>THERMAL - MECHANICAL SPECIFICATIONS</b>						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction to case	$R_{thJC}$		-	-	0.63	K/W
Thermal resistance, case to heatsink	$R_{thCS}$	Mounting surface, flat, smooth and greased	-	0.2	-	
Weight			-	5.5	-	g
			-	0.2	-	oz.
Mounting torque			1.2 (10)	-	2.4 (20)	N · m (lbf · in)
Marking device		Case style TO-247AC modified	60EPU06			
		Case style TO-247AC	60APU06			



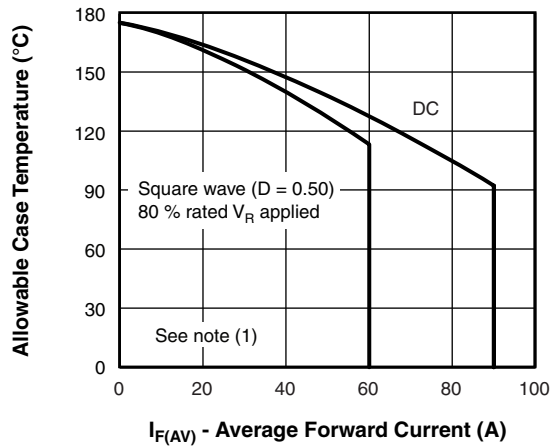


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

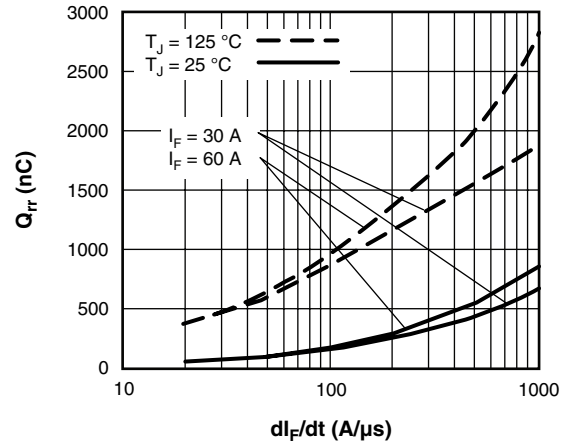


Fig. 7 - Typical Stored Charge vs.  $di_F/dt$

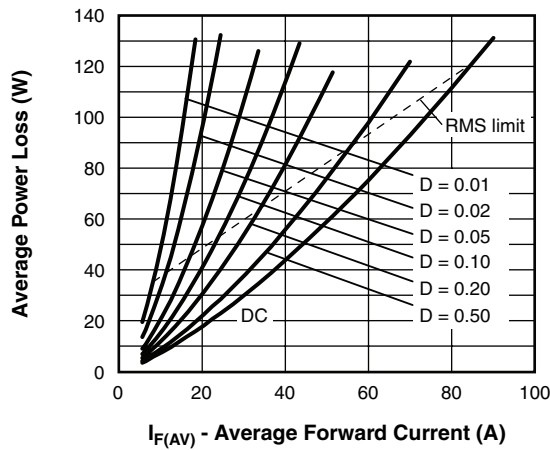


Fig. 6 - Forward Power Loss Characteristics

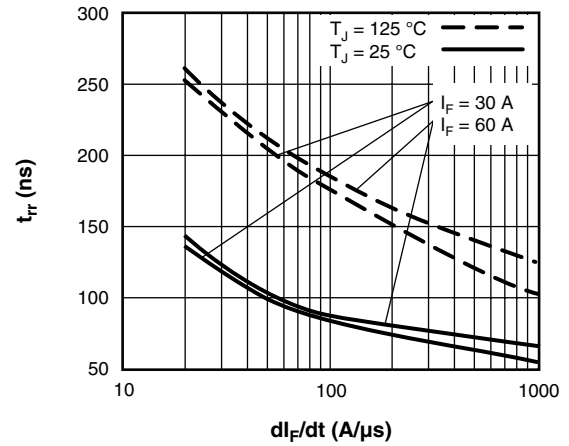


Fig. 8 - Typical Reverse Recovery Time vs.  $di_F/dt$

**Note**

- (1) Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;  
 $Pd$  = Forward power loss =  $I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 6);  
 $Pd_{REV}$  = Inverse power loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1} = 80\%$  rated  $V_R$

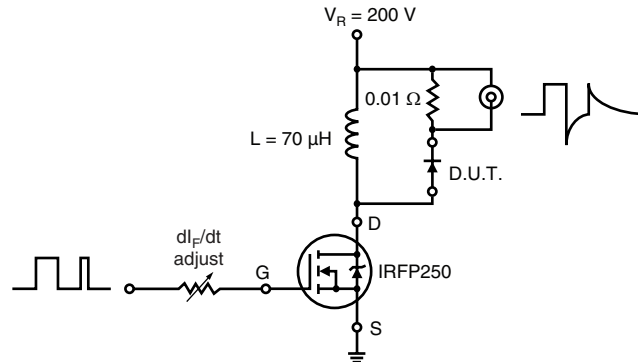
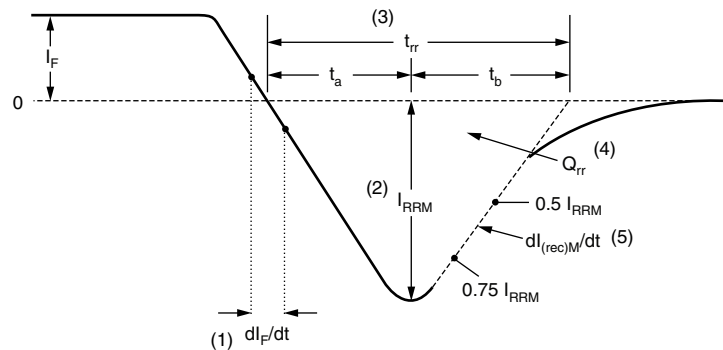


Fig. 9 - Reverse Recovery Parameter Test Circuit



- |   |   |
|---|---|
| <p>(1) <math>dl_F/dt</math> - rate of change of current through zero crossing</p> <p>(2) <math>I_{RRM}</math> - peak reverse recovery current</p> <p>(3) <math>t_{rr}</math> - reverse recovery time measured from zero crossing point of negative going <math>I_F</math> to point where a line passing through <math>0.75 I_{RRM}</math> and <math>0.50 I_{RRM}</math> extrapolated to zero current.</p> | <p>(4) <math>Q_{rr}</math> - area under curve defined by <math>t_{rr}</math> and <math>I_{RRM}</math></p> $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$ <p>(5) <math>dl_{(rec)M}/dt</math> - peak rate of change of current during <math>t_b</math> portion of <math>t_{rr}</math></p> |
|---|---|

Fig. 10 - Reverse Recovery Waveform and Definitions

## ORDERING INFORMATION TABLE

Device code	60	E	P	U	06	-
	①	②	③	④	⑤	⑥
①	-	Current rating (60 = 60 A)				
②	-	Circuit configuration: E = Single diode, 2 pins A = Single diode, 3 pins				
③	-	Package: P = TO-247AC modified				
④	-	Type of silicon: U = Ultrafast recovery				
⑤	-	Voltage rating (06 = 600 V)				
⑥	-	• None = Standard production • PbF = Lead (Pb)-free				

LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?95001">http://www.vishay.com/doc?95001</a>
Part marking information	<a href="http://www.vishay.com/doc?95006">http://www.vishay.com/doc?95006</a>



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